NSDEMN11XV6T1, NSDEMN11XV6T5

Common Cathode Quad Array Switching Diode

This Common Cathode Epitaxial Planar Quad Diode is designed for use in ultra high speed switching applications. This device is housed in the SOT−563 package which is designed for low power surface mount applications, where board space is at a premium.

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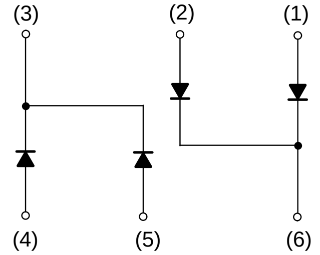
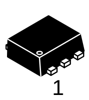
http://onsemi.com





SOT−563
CASE 463A
PLASTIC

Features

- Fast t_{rr}
- Low C_D
- Pb−Free Packages are Available

MAXIMUM RATINGS (T_A = 25°C)

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	80	Vdc
Peak Reverse Voltage	V_{RM}	80	Vdc
Forward Current	I_F	100	mAdc
Peak Forward Current	I_{FM}	300	mAdc
Peak Forward Surge Current	I_{FSM} (Note 1)	2.0	Adc

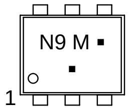
THERMAL CHARACTERISTICS

Characteristic (One Junction Heated)	Symbol	Max	Unit
Total Device Dissipation @T_A = 25°C Derate above 25°C	P_D	357 (Note 2) 2.9 (Note 2)	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	350 (Note 2)	°C/W
Characteristic (Both Junctions Heated)	**Symbol**	**Max**	**Unit**
Total Device Dissipation @T_A = 25°C Derate above 25°C	P_D	500 (Note 2) 4.0 (Note 2)	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	250 (Note 2)	°C/W
Junction and Storage Temperature	T_J, T_{stg}	−55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. t = 1 μS
2. FR−4 @ Minimum Pad

MARKING DIAGRAM



N9 = Specific Device Code
M = Date Code
▪ = Pb−Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
NSDEMN11XV6T1	SOT−563	4000/Tape & Reel
NSDEMN11XV6T1G	SOT−563 (Pb−Free)	4000/Tape & Reel
NSDEMN11XV6T5	SOT−563	8000/Tape & Reel
NSDEMN11XV6T5G	SOT−563 (Pb−Free)	8000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

May, 2006 − Rev. 2

ELECTRICAL CHARACTERISTICS (T_A = 25°C)

Characteristic	Symbol	Condition	Min	Max	Unit
Reverse Voltage Leakage Current	I_R	V_R = 70 V	−	0.1	μAdc
Forward Voltage	V_F	I_F = 100 mA	−	1.2	Vdc
Reverse Breakdown Voltage	V_R	I_R = 100 μA	80	−	Vdc
Diode Capacitance	C_D	V_R = 6.0 V, f = 1.0 MHz	−	3.5	pF
Reverse Recovery Time	t_{rr} (Note 3)	I_F = 5.0 mA, V_R = 6.0 V, R_L = 100 Ω, I_{rr} = 0.1 I_R	−	4.0	ns

3. t_{rr} Test Circuit on following page.

TYPICAL ELECTRICAL CHARACTERISTICS

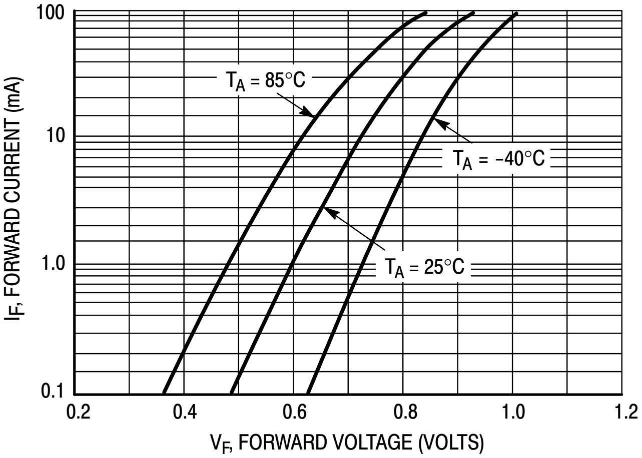


Figure 1. Forward Voltage

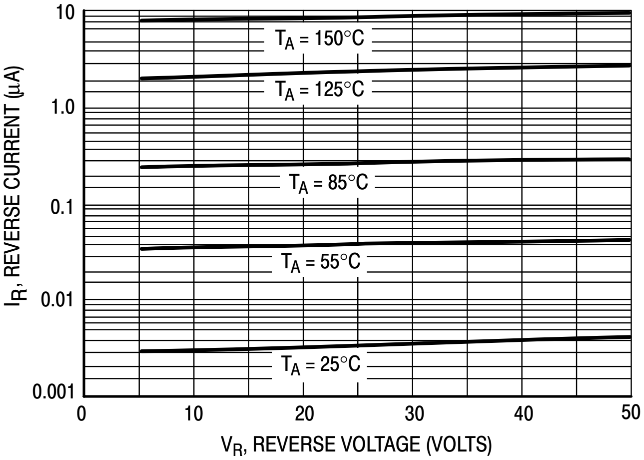


Figure 2. Reverse Current

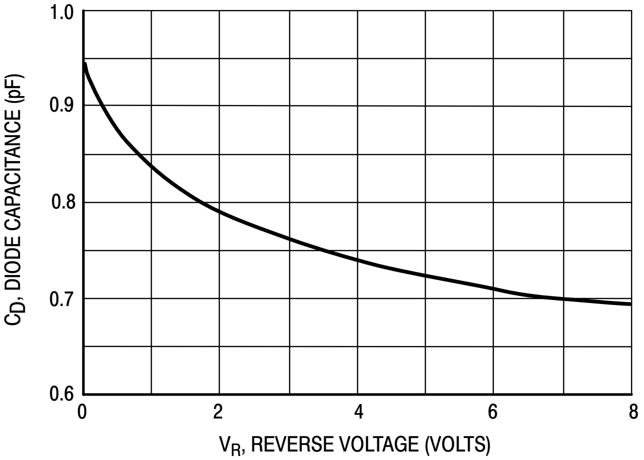
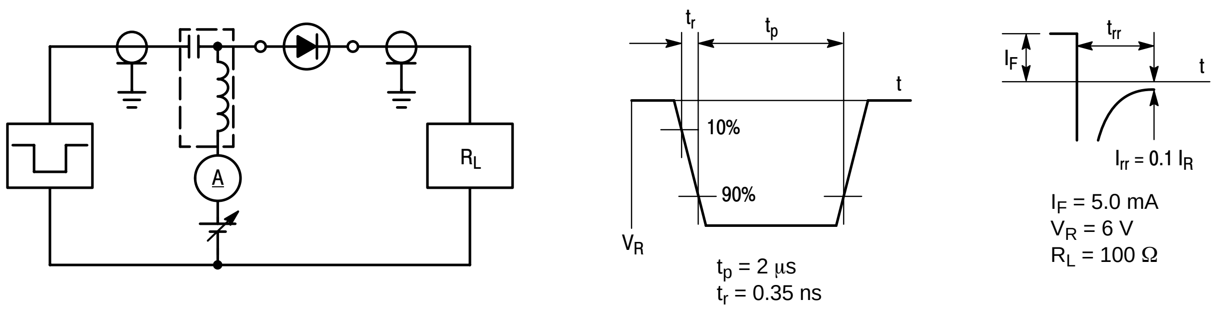
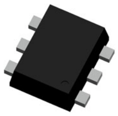


Figure 3. Diode Capacitance



RECOVERY TIME EQUIVALENT TEST CIRCUIT **INPUT PULSE** **OUTPUT PULSE**

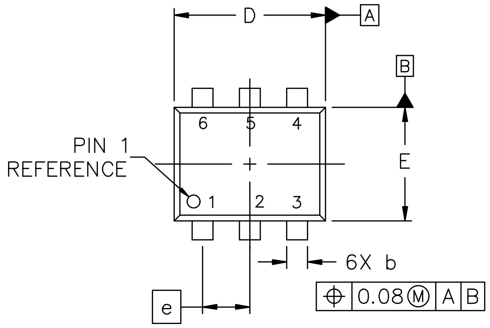
Figure 4. Reverse Recovery Time Test Circuit for the NSDEMN11XV6T1



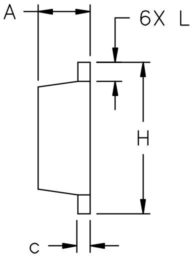
SOT-563-6 1.60x1.20x0.55, 0.50P
CASE 463A
ISSUE J

DATE 15 FEB 2024

NOTES:
1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5−2018.
2. ALL DIMENSION ARE IN MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

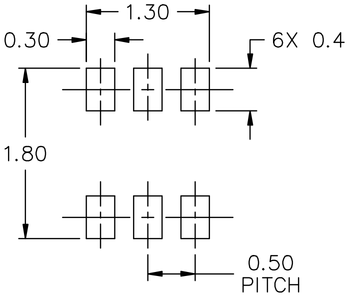


TOP VIEW



SIDE VIEW

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.50	0.55	0.60
b	0.17	0.22	0.27
c	0.08	0.13	0.18
D	1.50	1.60	1.70
E	1.10	1.20	1.30
e	0.50 BSC		
H	1.50	1.60	1.70
L	0.10	0.20	0.30



RECOMMENDED MOUNTING FOOTPRINT*

STYLE 1:
PIN 1. EMITTER 1
2. BASE 1
3. COLLECTOR 2
4. EMITTER 2
5. BASE 2
6. COLLECTOR 1

STYLE 2:
PIN 1. EMITTER 1
2. EMITTER 2
3. BASE 2
4. COLLECTOR 2
5. BASE 1
6. COLLECTOR 1

STYLE 3:
PIN 1. CATHODE 1
2. CATHODE 1
3. ANODE/ANODE 2
4. CATHODE 2
5. CATHODE 2
6. ANODE/ANODE 1

STYLE 4:
PIN 1. COLLECTOR
2. COLLECTOR
3. BASE
4. EMITTER
5. COLLECTOR
6. COLLECTOR

STYLE 5:
PIN 1. CATHODE
2. CATHODE
3. ANODE
4. ANODE
5. CATHODE
6. CATHODE

STYLE 6:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE

STYLE 7:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. ANODE
6. CATHODE

STYLE 8:
PIN 1. DRAIN
2. DRAIN
3. GATE
4. SOURCE
5. DRAIN
6. DRAIN

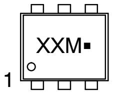
STYLE 9:
PIN 1. SOURCE 1
2. GATE 1
3. DRAIN 2
4. SOURCE 2
5. GATE 2
6. DRAIN 1

STYLE 10:
PIN 1. CATHODE 1
2. N/C
3. CATHODE 2
4. ANODE 2
5. N/C
6. ANODE 1

STYLE 11:
PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2

* FOR ADDITIONAL INFORMATION ON OUR Pb−FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XX = Specific Device Code
M = Month Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	**SOT−563−6 1.60x1.20x0.55, 0.50P**	**PAGE 1 OF 1**

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